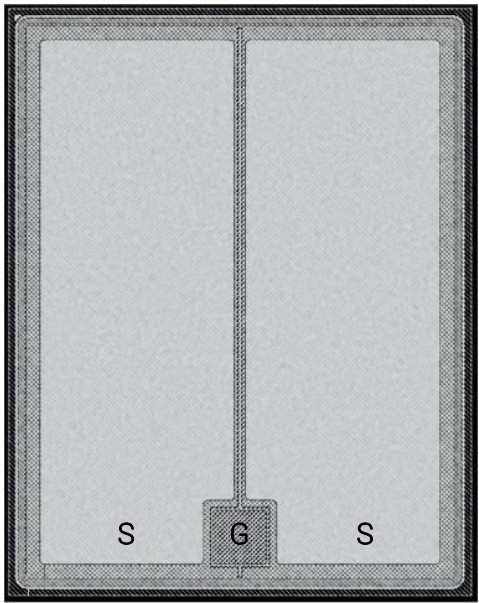


1200 V SiC MOSFET

TBM30116120

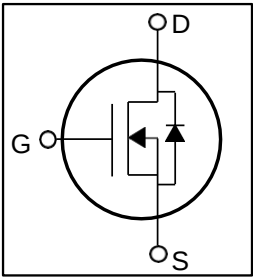
Coherent Silicon Carbide power MOSFET offers improved efficiency, higher switching frequency and industry-leading 200 °C rating.



FEATURES

- High voltage and low $R_{DS(ON)}$ up to 200 °C
- Fast switching enabled by ultra low gate resistance
- Very low, temperature invariant switching losses
- Avalanche ruggedness superior to silicon
- Fast recovery body diode for synchronous rectification

Chip dimensions: 5.1 mm X 6.5 mm		
J (A/cm ²)	133	265
I _{DS} (A)	43	85
R _{DS(ON)_SP} @175 °C (mΩ*mm ²)	734	746



- V_{DSS} = 1200 V
- $R_{DS(ON)}$ = 11.6 mΩ
- $T_{J,max}$ = 200 °C

MOSFET Static Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
I_D	Continuous Drain Current	$V_{GS} = 20\text{ V}, T_C = 25^\circ\text{C}, T_J = 200^\circ\text{C}$	-	-	175	A
		$V_{GS} = 20\text{ V}, T_C = 100^\circ\text{C}, T_J = 200^\circ\text{C}$	-	-	132	
		$V_{GS} = 20\text{ V}, T_C = 125^\circ\text{C}, T_J = 200^\circ\text{C}$	-	-	114	
$I_{D,pulse}$	Pulsed Drain Current ¹⁾	$T_C = 25^\circ\text{C}, T_J = 200^\circ\text{C}$	-	-	194	A
I_D	Continuous Drain Current	$V_{GS} = 20\text{ V}, T_C = 25^\circ\text{C}, T_J = 175^\circ\text{C}$	-	-	171	A
		$V_{GS} = 20\text{ V}, T_C = 100^\circ\text{C}, T_J = 175^\circ\text{C}$	-	-	121	
		$V_{GS} = 20\text{ V}, T_C = 125^\circ\text{C}, T_J = 175^\circ\text{C}$	-	-	99	
P_{tot}	Power Dissipation	$T_C = 25^\circ\text{C}$	-	-	765	W
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_{DS} = 32\text{ }\mu\text{A}$	1200	-	-	V
I_{DSS}	Drain Leakage Current	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$	-	-	32	μA
		$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}, T_J = 200^\circ\text{C}$	-	-	323	
I_{GSS}	Gate-Source Leakage Current	$V_{GS} = -15/23\text{ V}$	-	-	100	nA
V_{GS}	Recommended Gate-Source Voltage		-	20	-	V
$V_{GS,max}$	Maximum Gate-Source Voltage	$V_{DS} = 0\text{ V}$	-	-	-15/23	V
V_{TH}	Gate-Source Threshold Voltage	$V_{GS} = V_{DS}, I_{DS} = 32\text{ mA}, J = 0.1\text{ A/cm}^2, T_J = 25^\circ\text{C}$	2.0	2.8	4.0	V
		$V_{GS} = V_{DS}, I_{DS} = 32\text{ mA}, J = 0.1\text{ A/cm}^2, T_J = 175^\circ\text{C}$	1.4	2.2	3.4	
$R_{DS(ON)}$	Drain-Source On-Resistance	$V_{GS} = 20\text{ V}, I_{DS} = 43\text{ A}, J = 133\text{ A/cm}^2, T_J = 25^\circ\text{C}$	-	11.2	13.5	m Ω
		$V_{GS} = 20\text{ V}, I_{DS} = 115\text{ A}, J = 362\text{ A/cm}^2, T_J = 25^\circ\text{C}$	-	11.6	13.9	
		$V_{GS} = 20\text{ V}, I_{DS} = 43\text{ A}, J = 133\text{ A/cm}^2, T_J = 175^\circ\text{C}$	-	20.6	22.9	
		$V_{GS} = 20\text{ V}, I_{DS} = 85\text{ A}, J = 265\text{ A/cm}^2, T_J = 175^\circ\text{C}$	-	21.0	23.3	
		$V_{GS} = 20\text{ V}, I_{DS} = 115\text{ A}, J = 362\text{ A/cm}^2, T_J = 200^\circ\text{C}$	-	23.2	26.1	
$R_{GATE, ESR}$	Gate-Source Series Resistance	$V_{GS} = 0\text{ V}, \text{Drain Source Shorted}$	-	0.46	-	Ω
E_{AS}	Single Pulse Avalanche Energy	$I_D = 51\text{ A}, L = 4.7\text{ mH}$	-	5.9	-	J
$R_{th,JC}$	Thermal Resistance, Junction-Case	Assumes TO247-4L Packaged Die	-	0.2	0.22	$^\circ\text{C/W}$
T_J, T_{stg}	Bare chip/Discrete Max Junction Operating and Storage Temperature		-55	-	200	$^\circ\text{C}$

MOSFET Dynamic Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Units
C_{ISS}	Input Capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 500 \text{ V}, f = 100 \text{ kHz}$	-	6825	-	pF
C_{OSS}	Output Capacitance		-	320	-	
C_{RSS}	Reverse Transfer Capacitance		-	21	-	
$t_{d(on)}$	Turn-on Delay Time	$V_{DS} = 600 \text{ V}, V_{GS} = 0/20 \text{ V}, I_D = 40 \text{ A}, R_{G,ext} = 5.6 \Omega$	-	13	-	ns
t_r	Rise Time		-	12	-	
$t_{d(off)}$	Turn-off delay time		-	50	-	
t_f	Fall time		-	15	-	
E_{ON}	Turn-On Energy	$V_{DS} = 600 \text{ V}, V_{GS} = -5/20 \text{ V}, I_D = 115 \text{ A}, R_{G,ext} = 3.3 \Omega, L = 1.6 \text{ mH}, (\text{FWD}=\text{C4D10120})$	-	2.10	-	mJ
E_{OFF}	Turn-Off Energy		-	1.20	-	
E_{TOT}	Total Switching Energy		-	3.20	-	
Q_G	Total Gate Charge ²⁾	$V_{GS} = -5 \text{ to } 18 \text{ V}, I_{DS} = 60 \text{ A}, V_{DS} = 900 \text{ V}$	-	283	-	nC
Q_{GS}	Gate-Source Charge ²⁾		-	112	-	
Q_{GD}	Gate-Drain Charge ²⁾		-	76	-	

Diode Characteristics³⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Units
I_{SD}	Pulsed Body Diode Current	$V_{GS} = 0 \text{ V}$	-	-	162	A
V_{SD}	Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 115 \text{ A}$	-	3.9	-	V

¹⁾Pulse width limited by $T_{J,max}$

²⁾ Q_{GS} and Q_{GD} values were calculated using the two-curve extraction method shown in Fig. 12.

³⁾We recommend the use of body diode in synchronous rectification mode with repetitive conduction during switch commutation dead-time $\leq 1 \mu\text{s}$. Our long term (up to 13,000 hours) continuous switching test results show excellent reliability and forward voltage stability, indicating it is safe to use the body diode in this mode.

Figure 1. Output Characteristics
 $I_D = f(V_{DS}, V_{GS}); T_J = 25^\circ\text{C}$

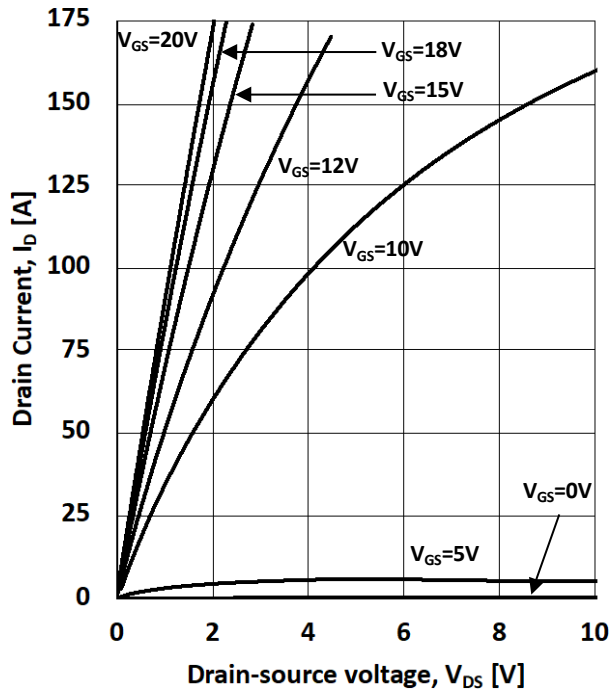


Figure 2. Output Characteristics
 $I_D = f(V_{DS}, V_{GS}); T_J = 200^\circ\text{C}$

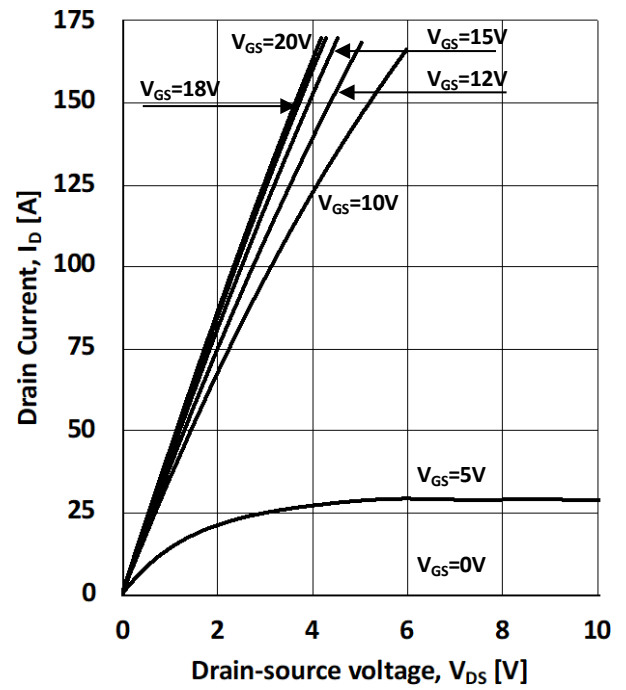


Figure 3. Threshold Voltage
 $V_t = f(T_J); V_{DS} = V_{GS}; I_D = 32\text{ mA}$

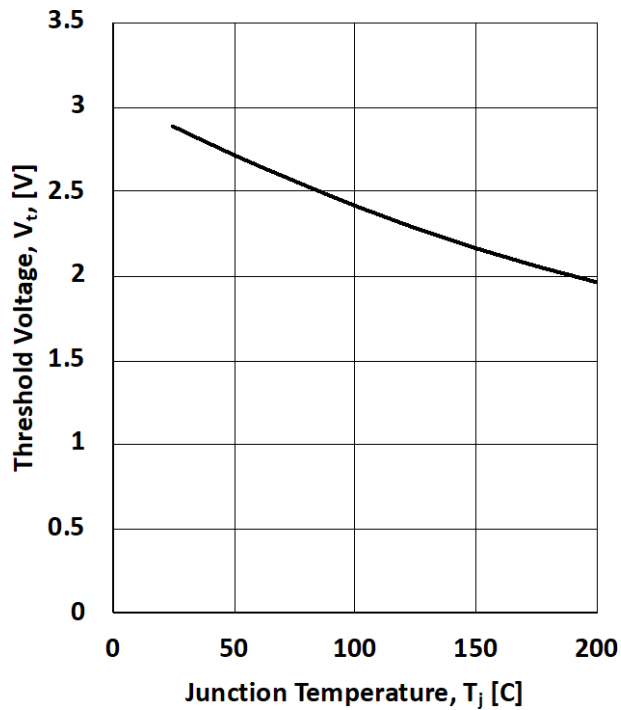


Figure 4. Drain-Source On-State Resistance
 $R_{DS(ON)} = f(T_J); I_D = 115\text{ A}$

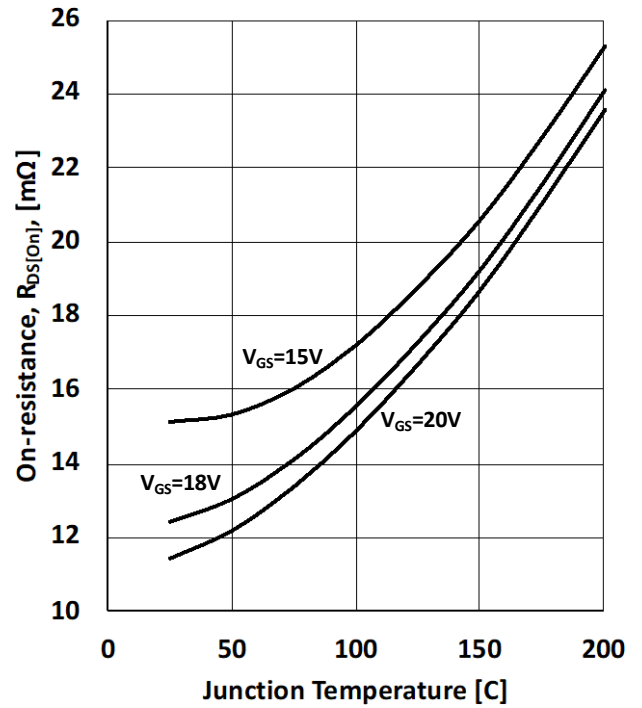


Figure 5. Drain-Source On-State Resistance
 $R_{DS(on)} = f(I_D); T_J = 25^\circ\text{C}$

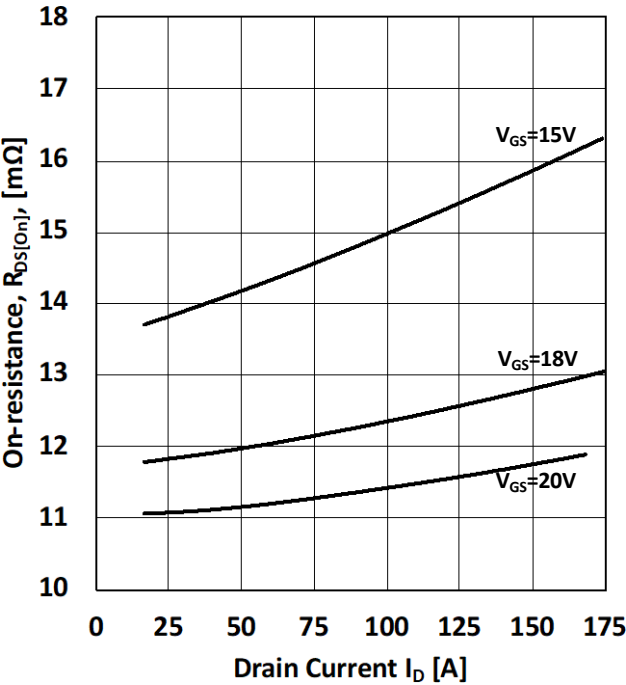


Figure 6. Drain-Source On-State Resistance
 $R_{DS(on)} = f(T_J); V_{GS} = 20\text{ V}$

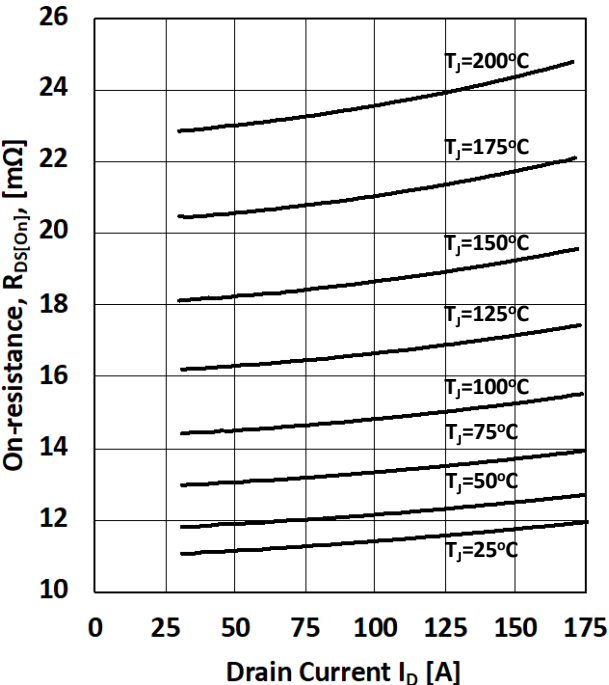


Figure 7. Third Quadrant Characteristics
 $I_D = f(V_{DS}, V_{GS}); T_J = 25^\circ\text{C}$

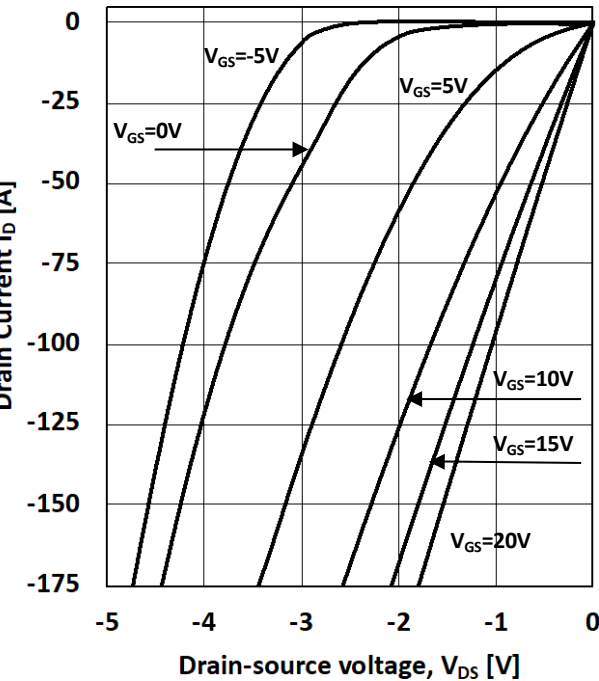


Figure 8. Third Quadrant Characteristics
 $I_D = f(V_{DS}, V_{GS}); T_J = 200^\circ\text{C}$

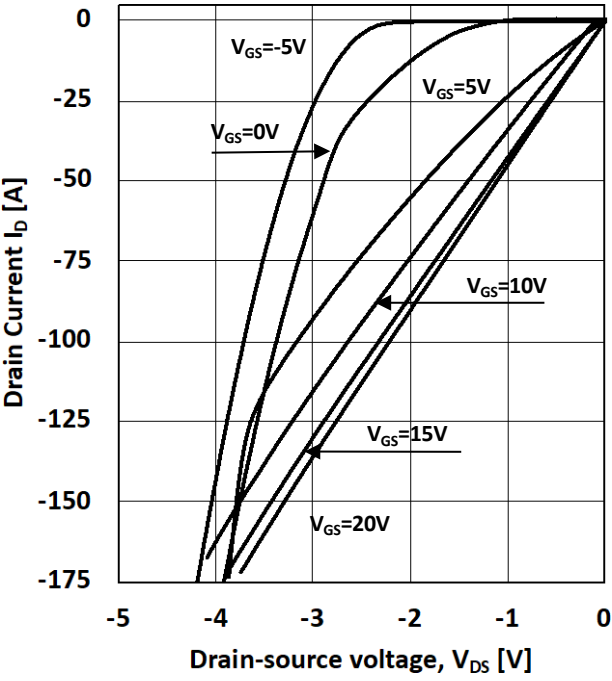


Figure 9. Capacitances
 $C = f(V_{DS})$; $f = 100 \text{ kHz}$

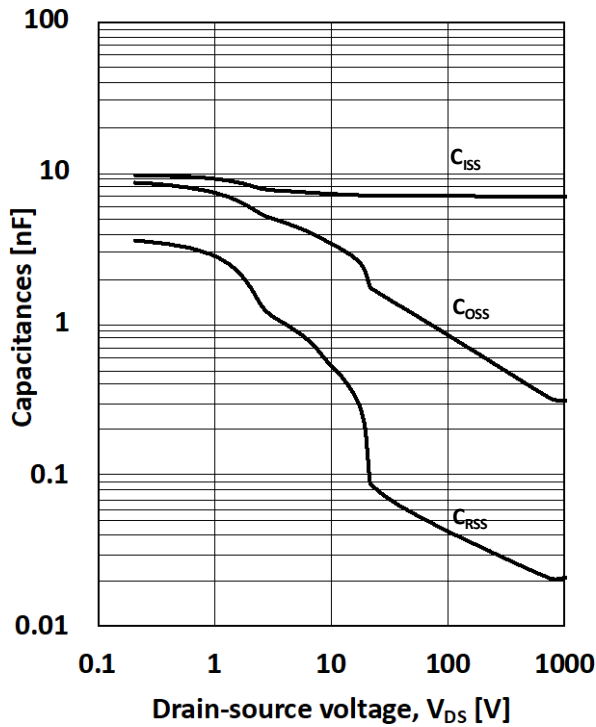


Figure 10. Clamped Inductive Switching Energy
 $E_{ON} = f(I_D)$; $E_{OFF} = f(I_D)$; $E_{TOT,SW} = f(I_D)$

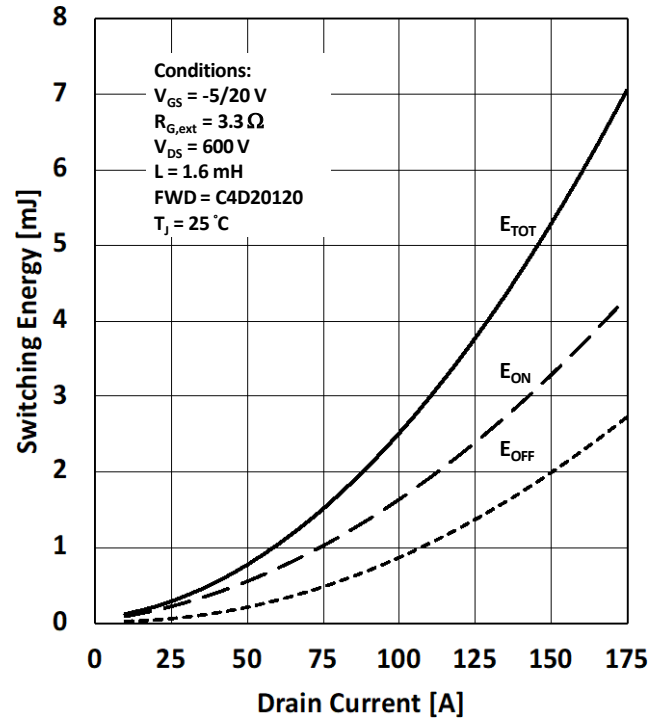


Figure 11. Typical Unclamped Inductive Switching Waveforms
 $I_D = f(t)$; $V_{DS} = f(t)$

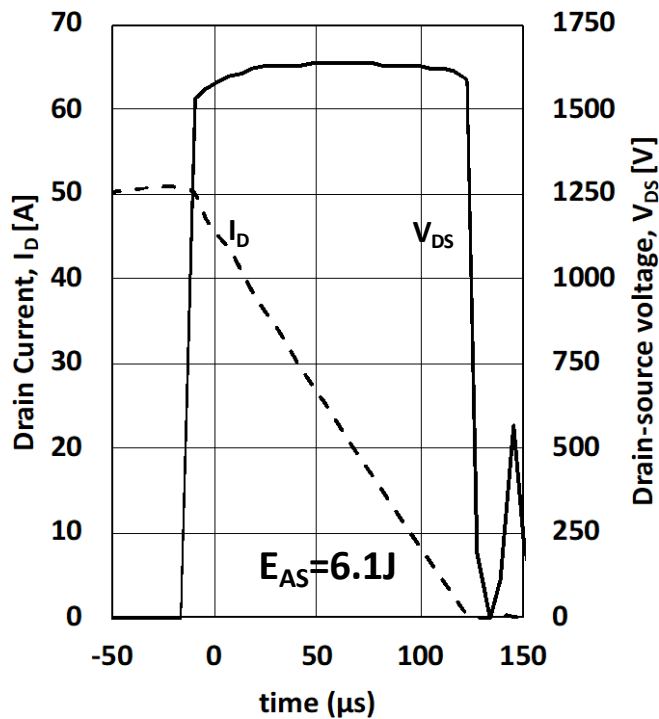


Figure 12. Gate Charge
 $V_{GS} = (-5 \dots +18 \text{ V})$; $V_{DS} = 900 \text{ V}$; $I_{DS} = 60 \text{ A}$; $T_J = 25 \text{ °C}$

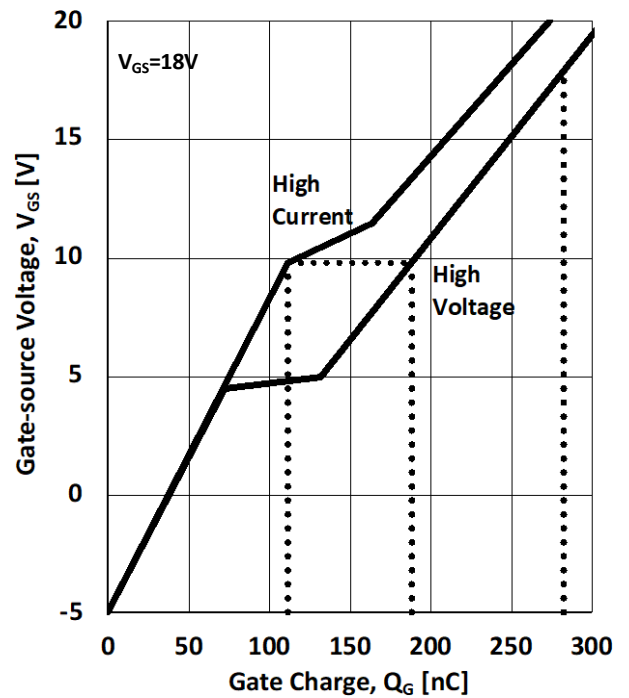


Figure 13. Transfer Characteristic
 $I_D = f(V_{GS})$; $V_{DS} = 10\text{ V}$; $T_J = 25^\circ\text{C}$

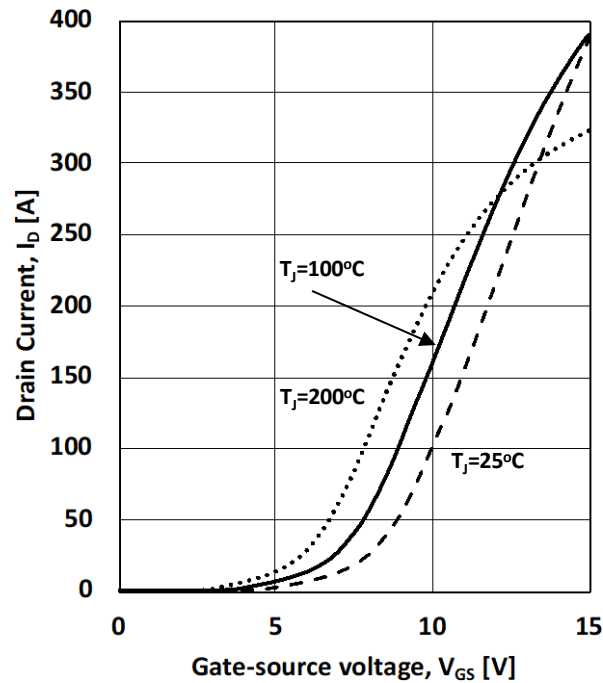


Figure 14. Clamped Inductive Switching Waveform Test Circuit

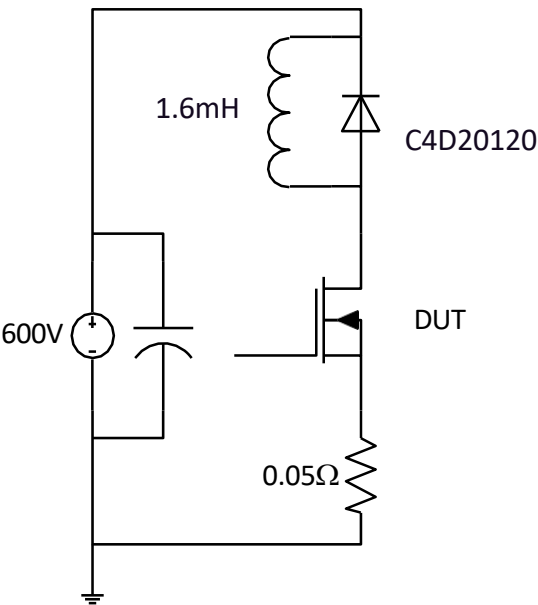


Figure 15. Switching Waveforms for Transition Times

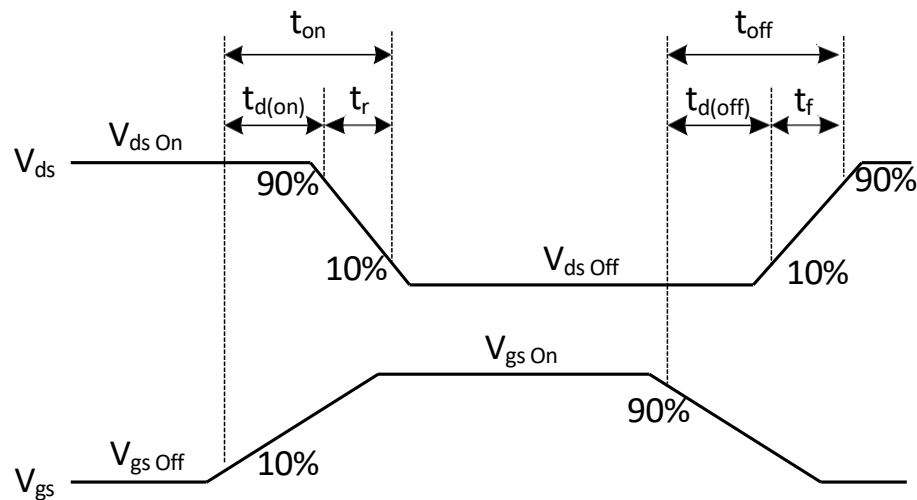
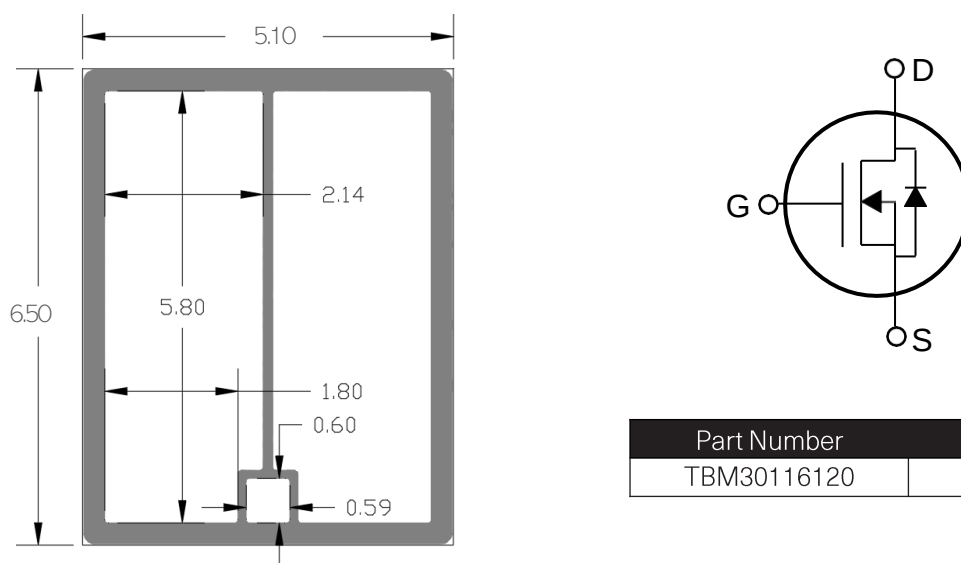


Figure 16. Chip Dimensions (mm)⁵⁾

Part Number	Package
TBM30116120	DIE

⁵⁾ Both source pads need to be wire-bonded, as they are not electrically connected on the chip

Mechanical Parameters

Parameter	Typical	Unit
Die Dimensions (L x W)	5.1 x 6.5 (± 0.05)	mm
Exposed Source Pad Metal Dimensions (2)	4.4 x 2.84 (± 0.05)	mm
Source Pad Metal Notch Around Gate Pad (2)	0.71 x 0.345 (± 0.05)	mm
Gate Pad Dimensions	0.6 x 0.6 (± 0.05)	mm
Chip Thickness	150 $\pm$ 15	μm
Frontside (Source) Metallization (Al-Cu) Thickness	5	μm
Frontside (Gate) Metallization (Al-Cu) Thickness	5	μm
Frontside Polyimide Thickness	≤ 14	μm
Backside (Drain) Metallization (Ni/Au) Thickness	1.5 / 0.15	μm

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